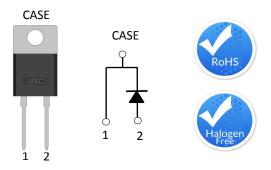
xR SiC Series | 5A - 1200V SiC Schottky Diode |

UJ2D1205T Datasheet

# Description

United Silicon Carbide, Inc. offers the xR series of high performance SiC Schottky diodes. With zero reverse recovery charge and 175°C maximum junction temperature, USCi's diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking		
UJ2D1205T	TO-220-2L	UJ2D1205T		

#### **Features**

- Positive temperature coefficient for safe operation and ease of paralleling
- 175°C maximum operating junction temperature
- Extremely fast switching not dependent on temperature
- Essentially no reverse or forward recovery
- RoHS compliant

# **Typical Applications**

- Power converters
- Industrial motor drives
- Switching-mode power supplies
- Power factor correction modules

## **Maximum Ratings**

Parameter	Symbol	Test Conditions	Value	Units	
DC blocking voltage	$V_R$		1200	V	
Repetitive peak reverse voltage, T <sub>j</sub> =25°C	$V_{RRM}$		1200	V	
Surge peak reverse voltage	V <sub>RSM</sub>		1200	V	
Maximum DC forward current	I <sub>F</sub>	T <sub>C</sub> = 151°C	5	А	
Non-repetitive forward surge current	I <sub>FSM</sub>	$T_C = 25$ °C, $t_p = 10$ ms	37.5	Α	
sine halfwave		$T_C = 110^{\circ}C$ , $t_p = 10$ ms	30		
Repetitive forward surge current	I <sub>FRM</sub>	$T_C = 25^{\circ}C, t_p = 10 \text{ms}$	21.3	A	
sine halfwave, D=0.1		$T_C = 110^{\circ}C$ , $t_p = 10$ ms	13		
Non-repetitive avalanche energy	E <sub>AS</sub>	T <sub>j</sub> = 25°C, L = 10mH, Ipk=2.9A, V <sub>DD</sub> =100V	44	mJ	
	P <sub>Tot</sub>	T <sub>C</sub> = 25°C	93	w	
Power dissipation		T <sub>C</sub> = 151°C	15		
Maximum junction temperature	$T_{J,max}$		175	°C	
Operating and storage temperature	T <sub>J</sub> , T <sub>STG</sub>		-55 to 175	°C	
Soldering temperatures, wavesoldering only allowed at leads	T <sub>sold</sub>	1.6mm from case for 10s	260	°C	



### **Electrical Characteristics**

 $T_1 = +25$ °C unless otherwise specified

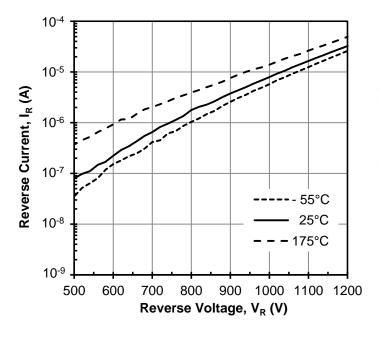
Davamakay	Cymphol	Test Conditions	Value			Haita
Parameter	Symbol		Min	Тур	Max	Units
Forward voltage	V	I <sub>F</sub> = 5A, T <sub>J</sub> = 25°C	-	1.5	1.7	V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 5A, T <sub>J</sub> =175°C	-	2.5	3	
Reverse current	1	V <sub>R</sub> =1200V, T <sub>j</sub> =25°C	-	30	190	μА
Reverse current	I <sub>R</sub>	V <sub>R</sub> =1200V, T <sub>J</sub> =175°C	-	60	600	
Total capacitive charge (1)	Q <sub>c</sub>	V <sub>R</sub> =800V		26		nC
		V <sub>R</sub> =1V, f=1MHz		260		pF
Total capacitance	С	V <sub>R</sub> =400V, f=1MHz		24		
		V <sub>R</sub> =800V, f=1MHz		19		
Capacitance stored energy	E <sub>C</sub>	V <sub>R</sub> =800V		6.8		μЈ

xR SiC Series |

#### Thermal characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Тур	Max	Ullits
Thermal resistance	$R_{\theta JC}$			1.19	1.6	°C/W

# **Typical Performance**

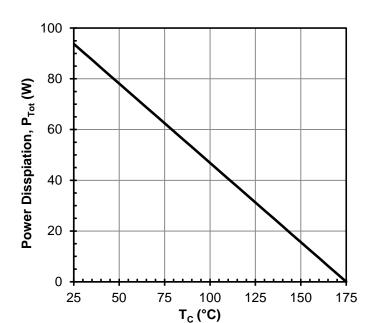


10 9 8 Forward Current, I<sub>F</sub> (A) 7 6 5 - 55°C 4 25°C 3 - 100°C 2 150°C 1 - 175°C 0 2 3 5 Forward Voltage, V<sub>F</sub> (V)

Figure 1 Typical reverse characteristics

Figure 2 Typical forward characteristics

<sup>(1)</sup> See Figure 8,  $Q_c$  is independent on  $T_i$ ,  $di_F/dt$ , and  $I_F$  as shown in the application note USCi\_AN0011.





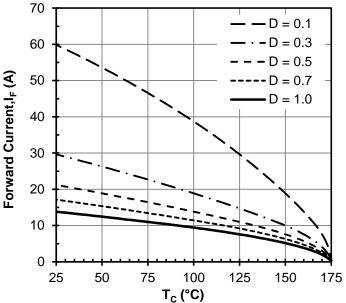
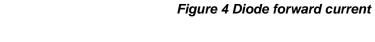
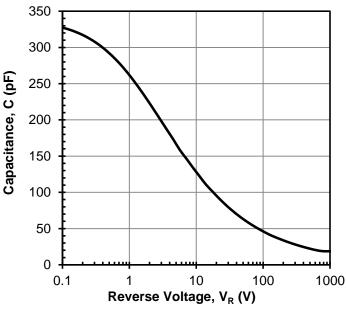


Figure 3 Power dissipation



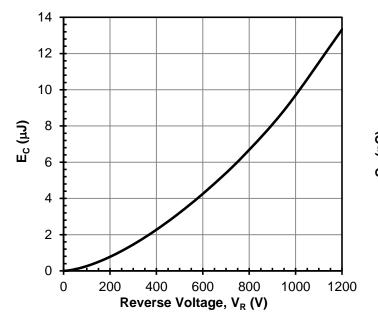


Max. Thermal Impedance, Z<sub>θJC</sub> (°C/W) • -D = 0.5D = 0.30.1 -D = 0.1--D = 0.05····· D = 0.02 Single Pulse 0.01 1.E-05 1.E-04 1.E-03 1.E-02 1.E-01 Time, t(s)

Figure 5 Capacitance vs. reverse voltage

Figure 6 Maximum transient thermal impedance

Datasheet



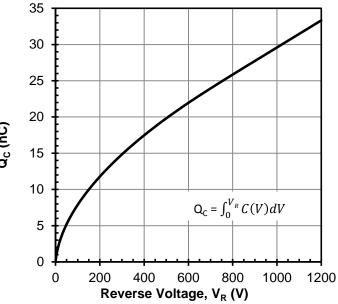


Figure 7 Typical capacitance stored energy vs. reverse voltage

Figure 8 Typical capacitive charge vs. reverse voltage

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